

# Taikyū Kim

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	High-Performance Indium Gallium Tin Oxide Transistors with an Al <sub>2</sub> O <sub>3</sub> Gate Insulator Deposited by Atomic Layer Deposition at a Low Temperature of 150 Å°C: Roles of Hydrogen and Excess Oxygen in the Al <sub>2</sub> O <sub>3</sub> Dielectric Film. ACS Applied Materials & Interfaces, 2021, 13, 28451-28461.	8.0	32
2	Lanthanum Doping Enabling High Drain Current Modulation in a p-Type Tin Monoxide Thin-Film Transistor. ACS Applied Materials & Interfaces, 2019, 11, 47025-47036.	8.0	26
3	Growth of high-quality semiconducting tellurium films for high-performance p-channel field-effect transistors with wafer-scale uniformity. Npj 2D Materials and Applications, 2022, 6, .	7.9	25
4	Material Design of New p-Type Tin Oxyselenide Semiconductor through Valence Band Engineering and Its Device Application. ACS Applied Materials & Interfaces, 2019, 11, 40214-40221.	8.0	17
5	Improved switching characteristics of p-type tin monoxide field-effect transistors through Schottky energy barrier engineering. Journal of Materials Chemistry C, 2020, 8, 201-208.	5.5	17
6	Recent Progress and Perspectives of Field-Effect Transistors Based on p-Type Oxide Semiconductors. Physica Status Solidi - Rapid Research Letters, 2022, 16, 2100394.	2.4	16
7	Improvement in performance of indium gallium oxide thin film transistor via oxygen mediated crystallization at a low temperature of 200Å°C. Ceramics International, 2022, 48, 12806-12812.	4.8	13
8	Origin of Ambipolar Behavior in p-Type Tin Monoxide Semiconductors: Impact of Oxygen Vacancy Defects. IEEE Transactions on Electron Devices, 2021, 68, 4467-4472.	3.0	12
9	High-Performance Broadband Phototransistor Based on TeO <sub>x</sub> /IGTO Heterojunctions. ACS Applied Materials & Interfaces, 2022, 14, 3008-3017.	8.0	8
10	Universal Metal-Interlayer-Semiconductor Contact Modeling Considering Interface-State Effect on Contact Resistivity Degradation. IEEE Transactions on Electron Devices, 2018, , 1-6.	3.0	2
11	P&#194: Late&#News&#Poster: Selenium 4p Orbital Enables High&#Mobility p&#Type Tin Oxyselenide Semiconductor for Thin&#Film Transistor Applications. Digest of Technical Papers SID International Symposium, 2020, 51, 1394-1396.	0.3	1
12	P&#198: Late&#News Poster: Off&#Current Reduction in p&#Type SnO Thin&#Film Transistors through Fermi&#Level Unpinning. Digest of Technical Papers SID International Symposium, 2019, 50, 1351-1353.	0.3	0
13	20&#4: <i>Student Paper:</i> High&#Performance p&#Channel Tellurium Thin&#Film Transistor Applications Fabricated at a Low Temperature of 150 Å°C. Digest of Technical Papers SID International Symposium, 2022, 53, 225-227.	0.3	0